# 8-Bit Addressable Latch/1-of-8 Decoder CMOS Logic Level Shifter

# With LSTTL-Compatible Inputs

The MC74LVX259 is an 8-bit Addressable Latch fabricated with silicon gate CMOS technology.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The LVX259 is designed for general purpose storage applications in digital systems. The device has four modes of operation as shown in the mode selection table. In the addressable latch mode, the data on Data In is written into the addressed latch. The addressed latch follows the data input with all non-addressed latches remaining in their previous states. In the memory mode, all latches remain in their previous state and are unaffected by the Data or Address inputs. In the one-of-eight decoding or demultiplexing mode, the addressed output follows the state of Data In with all other outputs in the LOW state. In the Reset mode, all outputs are LOW and unaffected by the address and data inputs. When operating the LVX259 as an addressable latch, changing more than one bit of the address could impose a transient wrong address. Therefore, this should only be done while in the memory mode.

The MC74LVX259 input structure provides protection when voltages up to 7.0 V are applied, regardless of the supply voltage. This allows the MC74LVX259 to be used to interface 5.0 V circuits to 3.0 V circuits.

#### **Features**

- High Speed:  $t_{PD} = 7.0 \text{ ns (Typ)}$  at  $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 2 \mu A$  (Max) at  $T_A = 25$ °C
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% \ V_{CC}$
- CMOS–Compatible Outputs:  $V_{OH} > 0.8 V_{CC}$ ;  $V_{OL} < 0.1 V_{CC}$  @Load
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

• These Devices are Pb-Free and are RoHS Compliant



## ON Semiconductor®

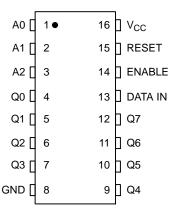
http://onsemi.com



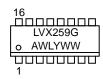


SOIC-16 D SUFFIX CASE 751B TSSOP-16 DT SUFFIX CASE 948F

#### **PIN ASSIGNMENT**



#### MARKING DIAGRAMS





SOIC-16

TSSOP-16

LVX259 = Specific Device Code A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

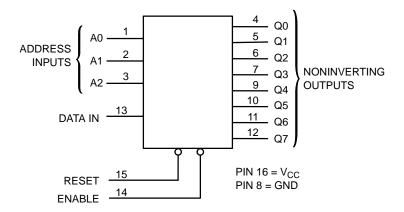


Figure 1. Logic Diagram

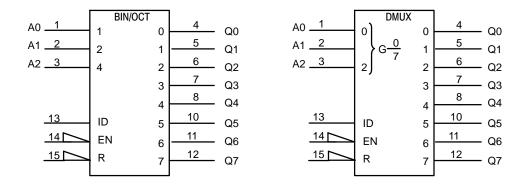


Figure 2. IEC Logic Symbol

#### **MODE SELECTION TABLE**

Enable	Reset	Mode
L	Н	Addressable Latch
Н	Н	Memory
L	L	8-Line Demultiplexer
Н	L	Reset

#### **LATCH SELECTION TABLE**

Addr	ess Ir	nputs	Latch
С	В	Α	Addressed
L	L	L	Q0
L	L	Н	Q1
L	Н	L	Q2
L	Н	Н	Q3
Н	L	L	Q4
Н	L	Н	Q5
Н	Н	L	Q6
Н	Н	Н	Q7

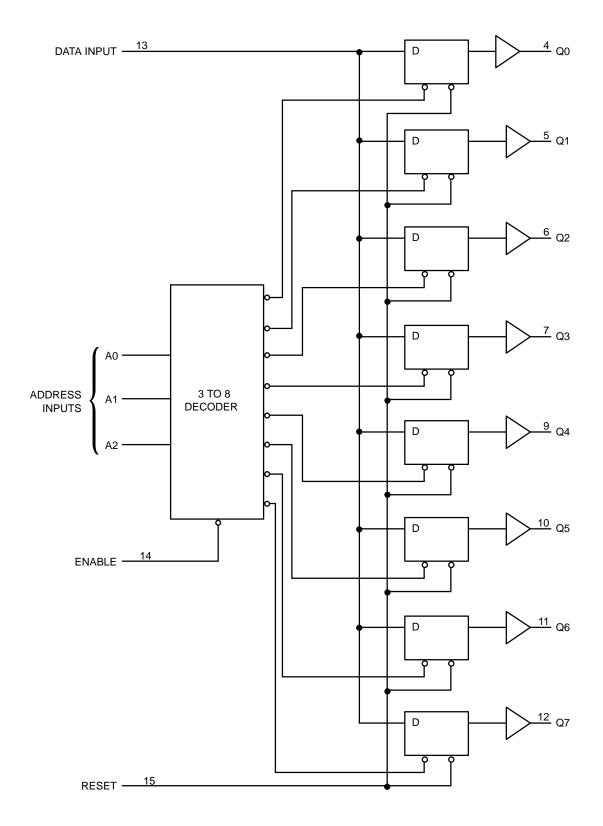


Figure 3. Expanded Logic Diagram

## **MAXIMUM RATINGS**

Symbol	Para	ameter	Value	Unit
V <sub>CC</sub>	Positive DC Supply Voltage		-0.5 to +7.0	V
V <sub>IN</sub>	Digital Input Voltage		-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage		-0.5 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Diode Current		-20	mA
I <sub>OK</sub>	Output Diode Current		±20	mA
I <sub>OUT</sub>	DC Output Current, per Pin		±25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins		±75	mA
P <sub>D</sub>	Power Dissipation in Still Air	SOIC Package TSSOP	200 180	mW
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	> 2000 > 200 > 2000	V
I <sub>LATCHUP</sub>	Latchup Performance	Above V <sub>CC</sub> and Below GND at 125°C (Note 4)	±300	mA
$\theta_{\sf JA}$	Thermal Resistance, Junction-to-Ambient	SOIC Package TSSOP	143 164	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Tested to EIA/JESD22–A114–A

- 2. Tested to EIA/JESD22-A115-A
  3. Tested to JESD22-C101-A
  4. Tested to EIA/JESD78

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage		2.0	3.6	V
V <sub>IN</sub>	DC Input Voltage		0	5.5	V
V <sub>OUT</sub>	DC Output Voltage		0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range, all Package Types		-40	85	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise or Fall Time $V_{CC} = 3.3 \text{ V}$	± 0.3 V	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## DC CHARACTERISTICS (Voltages Referenced to GND)

			V <sub>CC</sub>	T,	<sub>4</sub> = 25°	С	-40°C ≤ 1	Γ <sub>A</sub> ≤ 85°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 3.6	0.75 V <sub>CC</sub> 0.7 V <sub>CC</sub> 0.7 V <sub>CC</sub>	- - -	- - -	0.75 V <sub>CC</sub> 0.7 V <sub>CC</sub> 0.7 V <sub>CC</sub>	- - -	V
V <sub>IL</sub>	Maximum Low–Level Input Voltage		2.0 3.0 3.6	- - -	- - -	0.25 V <sub>CC</sub> 0.3 V <sub>CC</sub> 0.3 V <sub>CC</sub>	- - -	0.25 V <sub>CC</sub> 0.3 V <sub>CC</sub> 0.3 V <sub>CC</sub>	V
V <sub>OH</sub>	High-Level Output	$I_{OH} = -50 \mu A$	2.0	1.9	2.0	_	1.9	-	V
	Voltage	$I_{OH} = -50 \mu A$	3.0	2.9	3.0	_	2.9	-	
		$I_{OH} = -4 \text{ mA}$	3.0	2.58	_	_	2.48	_	
V <sub>OL</sub>	Low-Level Output	I <sub>OL</sub> = 50 μA	2.0	-	0.0	0.1	-	0.1	V
	Voltage	I <sub>OL</sub> = 50 μA	3.0	-	0.0	0.1	-	0.1	
		I <sub>OL</sub> = 4 mA	3.0	-	_	0.36	-	0.44	
I <sub>IN</sub>	Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 3.6	-	-	±0.1	-	±1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per package)	$V_{IN} = V_{CC}$ or GND	3.6	1.0	1.0	2.0	-	-	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## AC ELECTRICAL CHARACTERISTICS Input $t_r = t_f = 3.0 \text{ ns}$

					T <sub>A</sub> = 25°C	;	-40°C ≤	<b>T</b> <sub>A</sub> ≤ 85° <b>C</b>	
Symbol	Parameter	Test Conditi	ons	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Data to Output	V <sub>CC</sub> = 2.7 V	$C_L = 15pF$ $C_L = 50pF$	-	6.3 9.0	9.0 14.0	1.0 1.0	12.0 15.0	ns
	(Figures 4 and 8)	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$	-	5.6 8.0	8.0 12.0	1.0 1.0	11.0 14.0	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Address Select	V <sub>CC</sub> = 2.7 V	$C_L = 15pF$ $C_L = 50pF$	- 1	6.3 9.0	9.0 14.0	1.0 1.0	12.0 15.0	ns
	to Output (Figures 5 and 8)	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$	- 1	5.6 8.0	8.0 12.0	1.0 1.0	11.0 14.0	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Enable to Output	V <sub>CC</sub> = 2.7 V	$C_L = 15pF$ $C_L = 50pF$		6.3 9.0	9.0 14.0	1.0 1.0	12.0 15.0	ns
	(Figures 6 and 8)	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$	-	5.6 8.0	9.0 12.0	1.0 1.0	11.0 14.0	
t <sub>PHL</sub>	Maximum Propogation Delay, Reset to Output	V <sub>CC</sub> = 2.7 V	$C_L = 15pF$ $C_L = 50pF$	-	6.3 9.0	9.0 14.0	1.0 1.0	12.0 15.0	ns
	(Figures 6 and 8)	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$	-	5.6 8.0	9.0 12.0	1.0 1.0	11.0 14.0	
C <sub>IN</sub>	Maximum Input Capacitance			-	6	10	_	10	pF
					Typical	@ 25°C, \	V <sub>CC</sub> = 3.3 V	•	
$C_{PD}$	Power Dissipation Capac	itance (Note 5)				30			pF

<sup>5.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC} \cdot C_{PD}$  is used to determine the no–load dynamic power consumption;  $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$ .

**TIMING REQUIREMENTS** Input  $t_r = t_f = 3.0 \text{ ns}$ 

			1	Γ <sub>A</sub> = 25°0		<b>T</b> <sub>A</sub> = ≤	85°C	
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Unit
t <sub>w</sub>	Minimum Pulse Width, Reset or Enable	V <sub>CC</sub> = 2.7 V	4.5	_	-	5.0	-	ns
	(Figure 7)	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	4.5	_	-	5.0	-	
t <sub>su</sub>	Minimum Setup Time, Address or Data to Enable	V <sub>CC</sub> = 2.7 V	4.0	_	-	4.0	-	ns
	(Figure 7)	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	3.0	_	-	3.0	-	
t <sub>h</sub>	Minimum Hold Time, Enable to Address or Data	V <sub>CC</sub> = 2.7 V	2.0	_	-	2.0	-	ns
	(Figure 6 or 7)	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	2.0	_	-	2.0	-	
$t_{r,} t_{f}$	Maximum Input, Rise and Fall Times	V <sub>CC</sub> = 2.7 V	-	_	400	-	300	ns
	(Figure 4)	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	_	-	300	-	300	

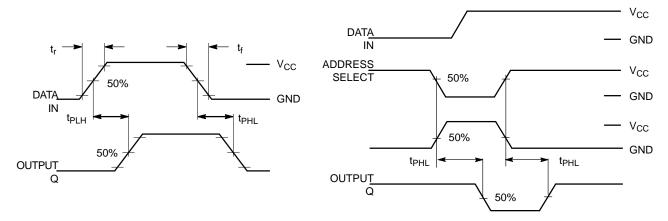


Figure 4. Switching Waveform

Figure 5. Switching Waveform

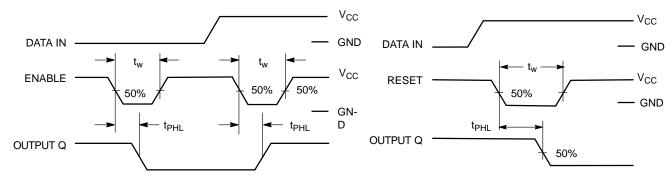


Figure 6. Switching Waveform

Figure 7. Switching Waveform

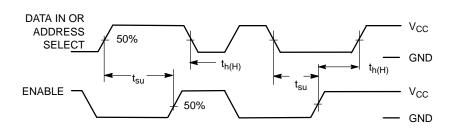
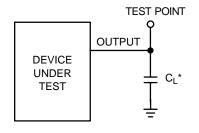


Figure 8. Switching Waveform



\*Includes all probe and jig capacitance

Figure 9. Test Circuit

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74LVX259DG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74LVX259DR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74LVX259DTG	TSSOP-16 (Pb-Free)	96 Units / Rail
MC74LVX259DTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# EMBOSSED CARRIER DIMENSIONS (See Notes 6 and 7)

Tape Size	B <sub>1</sub> Max	D	D <sub>1</sub>	E	F	К	Р	P <sub>0</sub>	P <sub>2</sub>	R	Т	w
8 mm	4.35 mm (0.179")	1.5 mm + 0.1 -0.0 (0.059"	1.0 mm Min (0.179")	1.75 mm ±0.1 (0.069 ±0.004")	3.5 mm ±0.5 (1.38 ±0.002")	2.4 mm Max (0.094")	4.0 mm ±0.10 (0.157 ±0.004")	4.0 mm ±0.1 (0.157 ±0.004")	2.0 mm ±0.1 (0.079 ±0.004")	25 mm (0.98")	0.6 mm (0.024)	8.3 mm (0.327)
12 mm	8.2 mm (0.323")	+0.004 -0.0)	1.5 mm Min (0.060)		5.5 mm ±0.5 (0.217 ±0.002")	6.4 mm Max (0.252")	4.0 mm ±0.10 (0.157 ±0.004") 8.0 mm ±0.10 (0.315 ±0.004")			30 mm (1.18")		12.0 mm ±0.3 (0.470 ±0.012")
16 mm	12.1 mm (0.476")				7.5 mm ±0.10 (0.295 ±0.004")	7.9 mm Max (0.311")	4.0 mm ±0.10 (0.157 ±0.004") 8.0 mm ±0.10 (0.315 ±0.004") 12.0 mm ±0.10 (0.472 ±0.004")					16.3 mm (0.642)
24 mm	20.1 mm (0.791")				11.5 mm ±0.10 (0.453 ±0.004")	11.9 mm Max (0.468")	16.0 mm ±0.10 (0.63 ±0.004")					24.3 mm (0.957)

Metric Dimensions Govern–English are in parentheses for reference only.
 A<sub>0</sub>, B<sub>0</sub>, and K<sub>0</sub> are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity



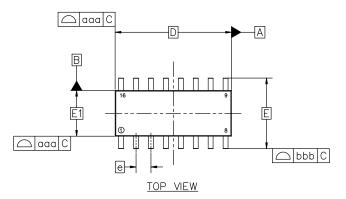


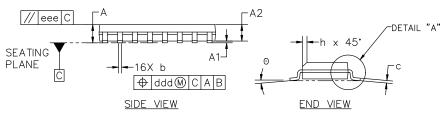
#### SOIC-16 9.90x3.90x1.50 1.27P CASE 751B ISSUE L

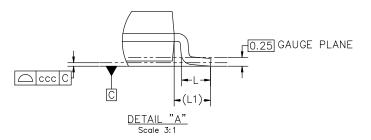
#### **DATE 29 MAY 2024**

#### NOTES:

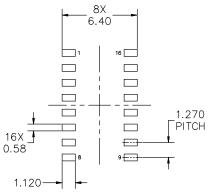
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
- 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
- DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE 6 DIMENSION AT MAXIMUM MATERIAL CONDITION.







	MILLIM	ETERS	
DIM	MIN	NOM	MAX
А	1.35	1.55	1.75
A1	0.00	0.05	0.10
A2	1.35	1.50	1.65
b	0.35	0.42	0.49
С	0.19	0.22	0.25
D		9.90 BSC	
E		6.00 BSC	
E1		3.90 BSC	
е		1.27 BSC	
h	0.25		0.50
L	0.40	0.83	1.25
L1		1.05 REF	
Θ	0.		7°
TOLERAN	CE OF FC	RM AND	POSITION
aaa		0.10	
bbb		0.20	
ccc		0.10	
ddd		0.25	
eee		0.10	



#### RECOMMENDED MOUNTING FOOTPRINT

\*FOR ADDITIONAL INFORMATION ON OUR
PB-FREE STRATEGY AND SOLDERING DETAILS,
PLEASE DOWNLOAD THE onsemi SOLDERING
AND MOUNTING TECHNIQUES REFERENCE
MANUAL, SOLDERRM/D

DOCUMENT NUMBER:	98ASB42566B	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED"	
DESCRIPTION:	SOIC-16 9.90X3.90X1.50 1	.27P	PAGE 1 OF 2

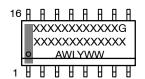
onsemi and ONSemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.



#### SOIC-16 9.90x3.90x1.50 1.27P CASE 751B ISSUE L

**DATE 29 MAY 2024** 

# GENERIC MARKING DIAGRAM\*



XXXXX = Specific Device Code

A = Assembly Location

WL = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

077/15/		077/15.0		071/15 0		T	
STYLE 1: PIN 1.	COLLECTOR	STYLE 2:	CATHODE	STYLE 3: PIN 1.		TYLE 4: PIN 1.	COLLECTOR DVF #1
PIN 1. 2.		PIN 1. 2.		PIN 1. 2.	COLLECTOR, DYE #1 BASE, #1	2.	
2. 3.	EMITTER	2. 3.	NO CONNECTION				
				3.		3.	
4.	NO CONNECTION	4.		4.		4.	
5.	EMITTER	5.		5.		5.	
6.	BASE	6.		6.		6.	
7.		7.			EMITTER, #2		COLLECTOR, #4
8.		8.		8.			COLLECTOR, #4
9.		9.			COLLECTOR, #3		BASE, #4
10.			ANODE		BASE, #3		EMITTER, #4
	NO CONNECTION	11.			EMITTER, #3		BASE, #3
	EMITTER		CATHODE		COLLECTOR, #3		EMITTER, #3
	BASE		CATHODE		COLLECTOR, #4		BASE, #2
	COLLECTOR	14.			BASE, #4		EMITTER, #2
15.			ANODE		EMITTER, #4		BASE, #1
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1
STYLE 5:		STYLE 6:		STYLE 7:			
STYLE 5: PIN 1.	DRAIN, DYE #1	STYLE 6: PIN 1.	CATHODE	STYLE 7: PIN 1.	SOURCE N-CH		
	DRAIN, DYE #1 DRAIN, #1			PIN 1.	SOURCE N-CH COMMON DRAIN (OUTPUT)		
PIN 1.	,	PIN 1.	CATHODE	PIN 1.	COMMON DRAIN (OUTPUT)		
PIN 1. 2.	DRAIN, #1	PIN 1. 2.	CATHODE CATHODE	PIN 1. 2.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3.	DRAIN, #1 DRAIN, #2	PIN 1. 2. 3.	CATHODE CATHODE	PIN 1. 2. 3.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4.	DRAIN, #1 DRAIN, #2 DRAIN, #2	PIN 1. 2. 3. 4.	CATHODE CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3	PIN 1. 2. 3. 4. 5.	CATHODE CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4. 5.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4	PIN 1. 2. 3. 4. 5.	CATHODE CATHODE CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4. 5.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3	PIN 1. 2. 3. 4. 5. 6.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4. 5. 6.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH		
PIN 1. 2. 3. 4. 5. 6. 7.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4	PIN 1. 2. 3. 4. 5. 6. 7.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 SOURCE, #4	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 SOURCE, #4	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GOMMON DRAIN (OUTPUT) GATE N-CH		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2 SOURCE, #2 SOURCE, #2	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) CATE N-CH COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT)		

DOCUMENT NUMBER:	98ASB42566B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOIC-16 9.90X3.90X1.50 1.27P		PAGE 2 OF 2	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

2X L/2

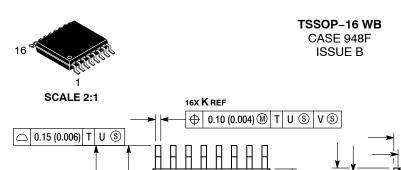
L

☐ 0.15 (0.006)

PIN 1 IDENT.

υ®





**DATE 19 OCT 2006** 

#### NOTES

Κ

SECTION N-N

0.25 (0.010)

J1

В

-U-

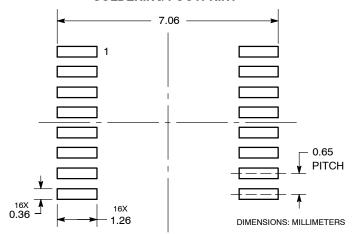
- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE
  INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL
  NOT EXCEED 0.25 (0.010) PER SIDE.
  DIMENSION K DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABILE DAMBAR
  PROTRUSION SHALL BE 0.08 (0.003) TOTAL
  IN EXCESS OF THE K DIMENSION AT
  MAXIMUM MATERIAL CONDITION.
  TERMINIAL NILMBERS ADE SUCIUMI ECIP.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
7	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	00	00	00	00

# **DETAIL E** -W-☐ 0.10 (0.004) **DETAIL E** SEATING PLANE D

#### **RECOMMENDED** SOLDERING FOOTPRINT\*

-V-



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC** MARKING DIAGRAM\*



= Specific Device Code XXXX Α = Assembly Location

= Wafer Lot L = Year W = Work Week G or • = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98ASH70247A	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TSSOP-16		PAGE 1 OF 1	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI., and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems. or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales